MICROWAVE POWER GAAS FET

TIM6472-35SL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 45.5dBm at 6.4GHz to 7.2GHz

·HIGH GAIN

G1dB= 8.0dB at 6.4GHz to 7.2GHz

·LOW INTERMODULATION DISTORTION

IM3(MIN.) = -42dBc at Pout= 35dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 8.0A f= 6.4 to 7.2GHz Two-Tone Test Po= 35dBm, Δf= 5MHz (Single Carrier Level)	dBm	45.0	45.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	7.0	8.0	_
Drain Current	IDS1		Α	_	8.0	9.0
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%	_	37	
3rd Order Intermodulation Distortion	IM3		dBc	-42	-45	
Drain Current	IDS2		Α	_	8.0	9.0
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.5A	S	_	6.5	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 140mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	20	_
Gate-Source Breakdown Voltage	VGSO	IGS= -420 _μ A	V	-5		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.3

- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

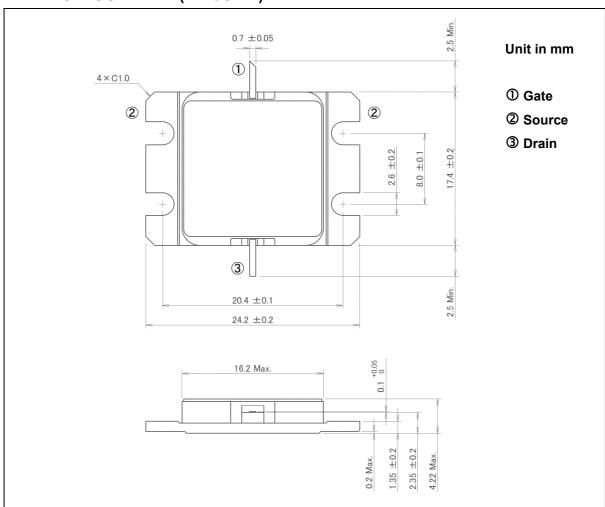
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25°C)	PT	W	115.4
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

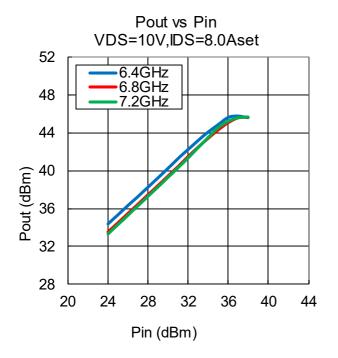
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

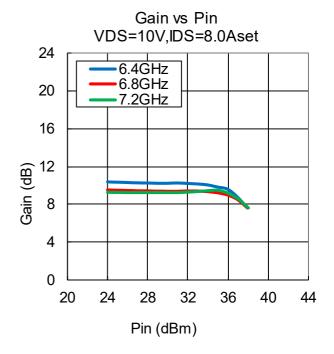


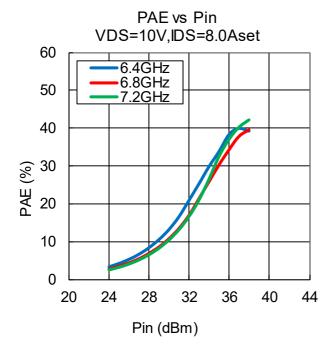
TYPICAL RF PERFORMANCE

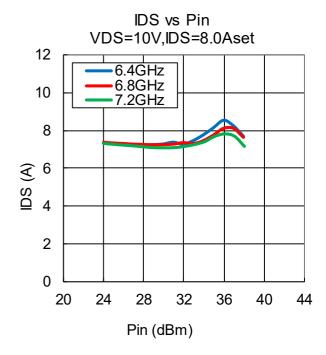
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 8.0 A, f= 6.4, 6.8, 7.2 GHz, Ta= +25 °C





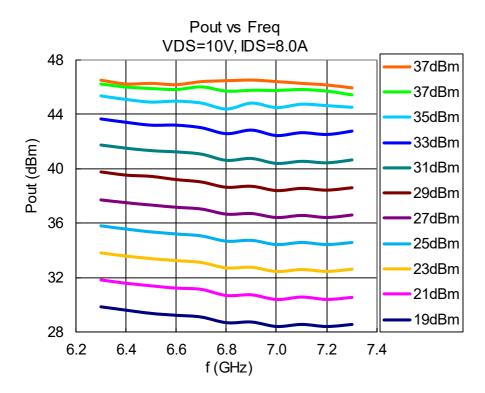






·Pout vs. Frequency

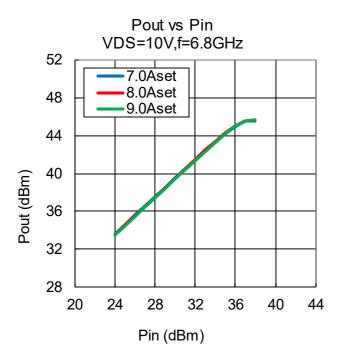
VDS= 10 V, IDSset= 8.0 A, Ta= +25 °C

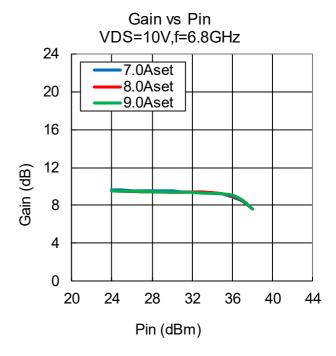


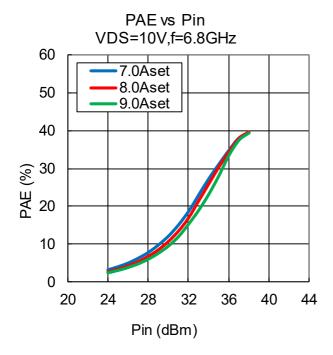


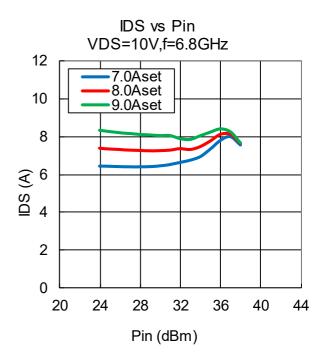
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 7.0, 8.0, 9.0 A, f= 6.8 GHz, Ta= +25 °C





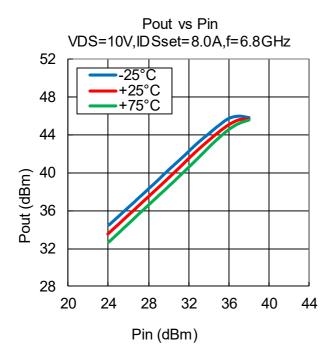


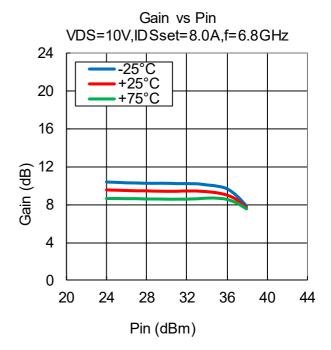


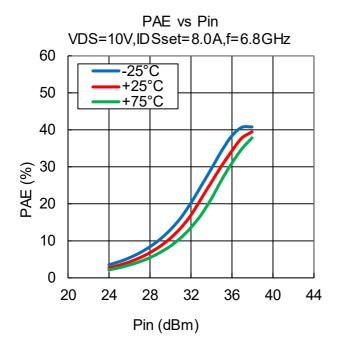


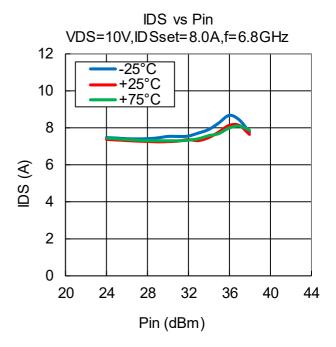
·Pout, Gain, PAE, IDS vs. Pin vs. Temperature

VDS= 1 0 V, IDSset= 8.0 A, f= 6.8 GHz, Ta= -25, +25, +75 °C





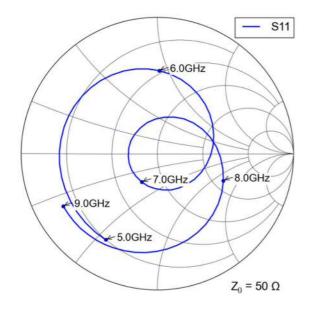


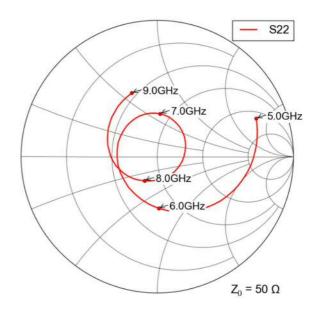


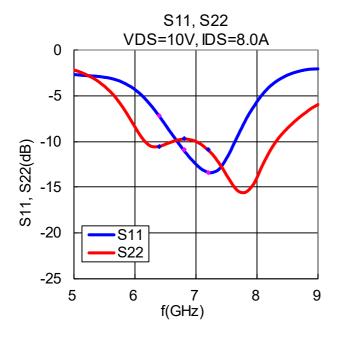


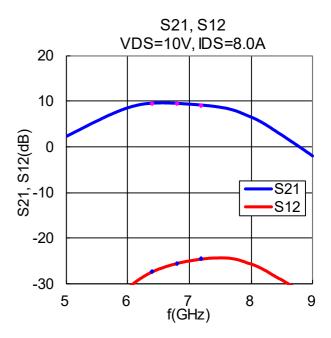
·S-Parameters

VDS= 10 V, IDSset= 8.0 A, f= 5.0 to 9.0 GHz, Ta= +25 $^{\circ}$ C











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